

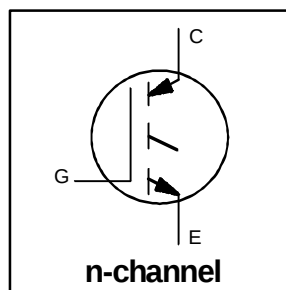
IRGPH20M

INSULATED GATE BIPOLAR TRANSISTOR

Short Circuit Rated
Fast IGBT

Features

- Short circuit rated - 10 μ s @ 125°C, $V_{GE} = 15V$
- Switching-loss rating includes all "tail" losses
- Optimized for medium operating frequency (1 to 10kHz) See Fig. 1 for Current vs. Frequency curve



$$V_{CES} = 1200V$$

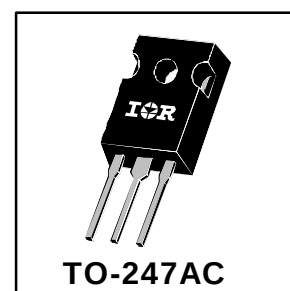
$$V_{CE(sat)} \leq 4.6V$$

$$@V_{GE} = 15V, I_C = 4.5A$$

Description

Insulated Gate Bipolar Transistors (IGBTs) from International Rectifier have higher usable current densities than comparable bipolar transistors, while at the same time having simpler gate-drive requirements of the familiar power MOSFET. They provide substantial benefits to a host of high-voltage, high-current applications.

These new short circuit rated devices are especially suited for motor control and other applications requiring short circuit withstand capability.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	6.9	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	4.5	
I_{CM}	Pulsed Collector Current ①	14	
I_{LM}	Clamped Inductive Load Current ②	14	
t_{sc}	Short Circuit Withstand Time	10	μ s
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	5.0	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	60	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	24	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	2.1	$^\circ C/W$
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	40	
Wt	Weight	—	6 (0.21)	—	g (oz)

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	20	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	1.3	—	V/ $^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	3.1	4.6	V	$I_C = 4.5A, V_{GE} = 15V$
		—	3.9	—		$I_C = 6.9A$ See Fig. 2, 5
		—	4.0	—		$I_C = 4.5A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	5.5		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/ $^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ⑤	1.3	2.6	—	S	$V_{CE} = 100V, I_C = 4.5A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 1200V$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 1200V, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	16	24	nC	$I_C = 4.5A$ $V_{CC} = 400V$ See Fig. 8 $V_{GE} = 15V$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	4.4	7.0		
Q_{gc}	Gate - Collector Charge (turn-on)	—	5.5	8.3		
$t_{d(on)}$	Turn-On Delay Time	—	26	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 4.5A, V_{CC} = 960V$ $V_{GE} = 15V, R_G = 50\Omega$ Energy losses include "tail"
t_r	Rise Time	—	13	—		
$t_{d(off)}$	Turn-Off Delay Time	—	43	65		
t_f	Fall Time	—	430	640		
E_{on}	Turn-On Switching Loss	—	0.33	—	mJ	See Fig. 9, 10, 11, 14
E_{off}	Turn-Off Switching Loss	—	0.78	—		
E_{ts}	Total Switching Loss	—	1.1	1.7		
t_{sc}	Short Circuit Withstand Time	10	—	—	μs	$V_{CC} = 720V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 50\Omega, V_{CPK} < 1000V$
$t_{d(on)}$	Turn-On Delay Time	—	32	—	ns	$T_J = 150^\circ\text{C},$ $I_C = 4.5A, V_{CC} = 960V$ $V_{GE} = 15V, R_G = 50\Omega$ Energy losses include "tail"
t_r	Rise Time	—	20	—		
$t_{d(off)}$	Turn-Off Delay Time	—	480	—		
t_f	Fall Time	—	450	—		
E_{ts}	Total Switching Loss	—	2.4	—	mJ	See Fig. 10, 14
L_E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	340	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ See Fig. 7 $f = 1.0MHz$
C_{oes}	Output Capacitance	—	25	—		
C_{res}	Reverse Transfer Capacitance	—	4.7	—		

Notes:

- ① Repetitive rating; $V_{GE}=20V$, pulse width limited by max. junction temperature. (See fig. 13b)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G=50\Omega$, (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ⑤ Pulse width $5.0\mu s$, single shot.

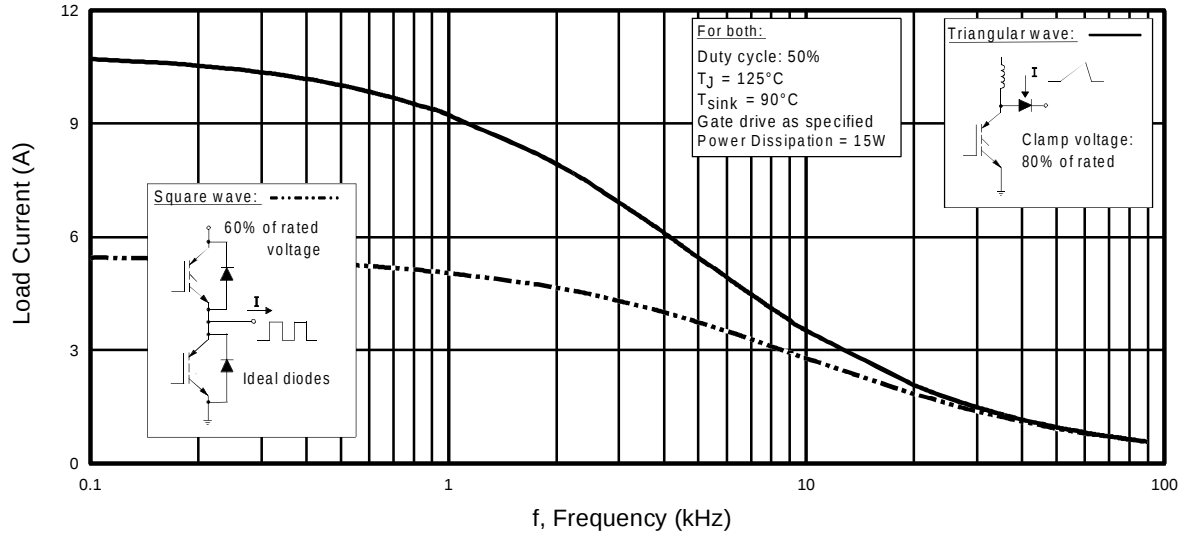


Fig. 1 - Typical Load Current vs. Frequency
(For square wave, $I = I_{\text{RMS}}$ of fundamental; for triangular wave, $I = I_{\text{PK}}$)

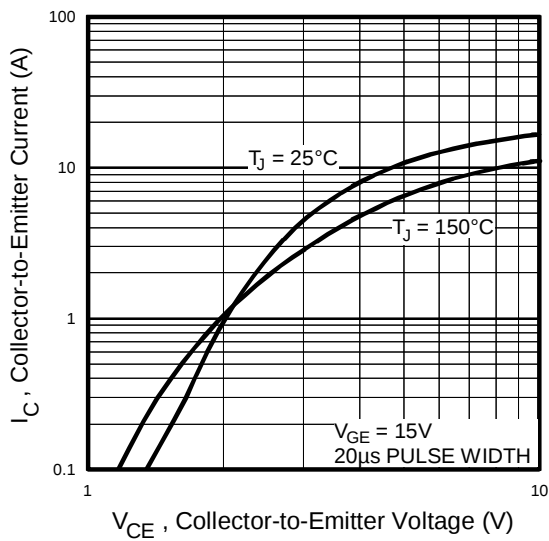


Fig. 2 - Typical Output Characteristics

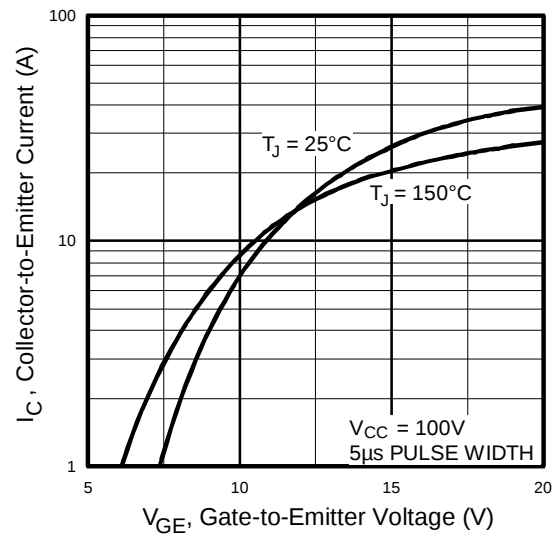


Fig. 3 - Typical Transfer Characteristics

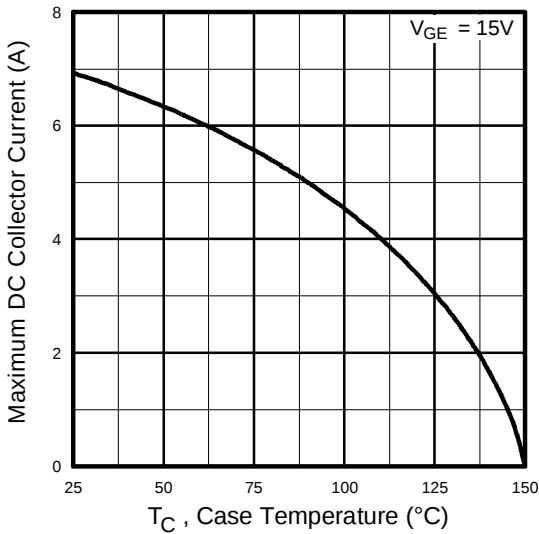


Fig. 4 - Maximum Collector Current vs. Case Temperature

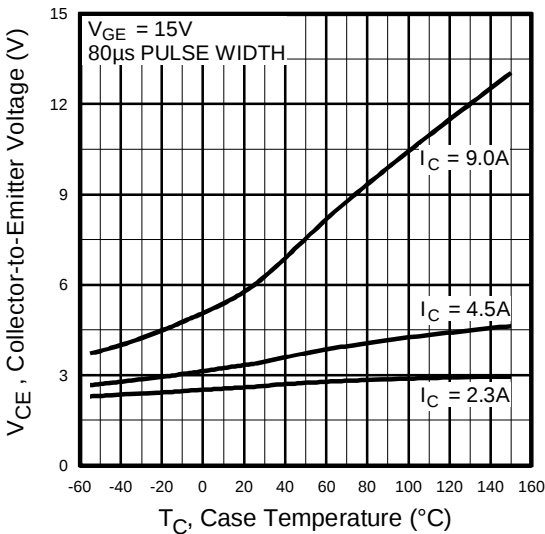


Fig. 5 - Collector-to-Emitter Voltage vs. Case Temperature

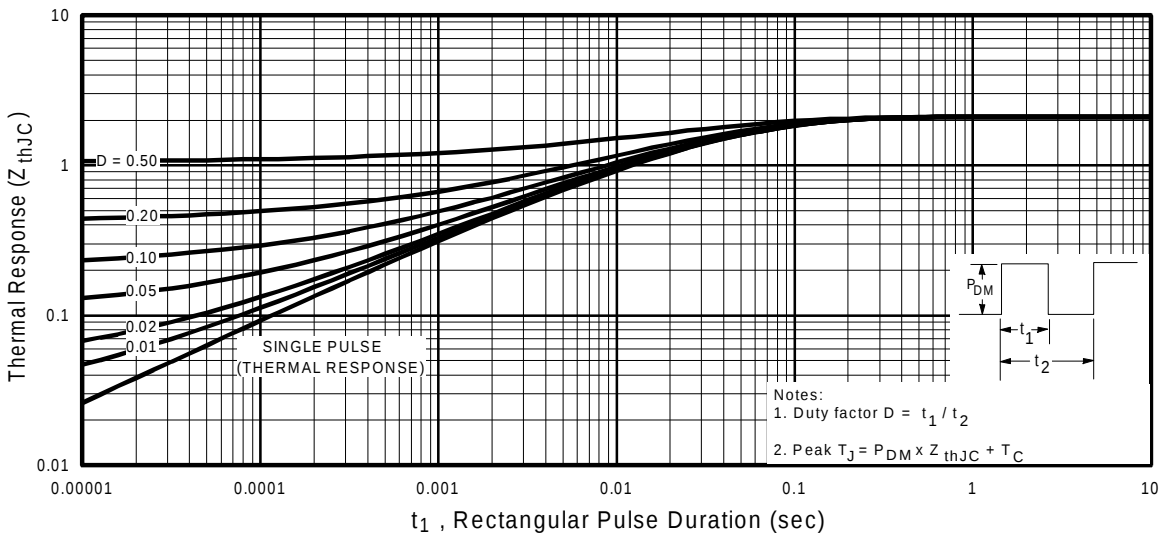


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

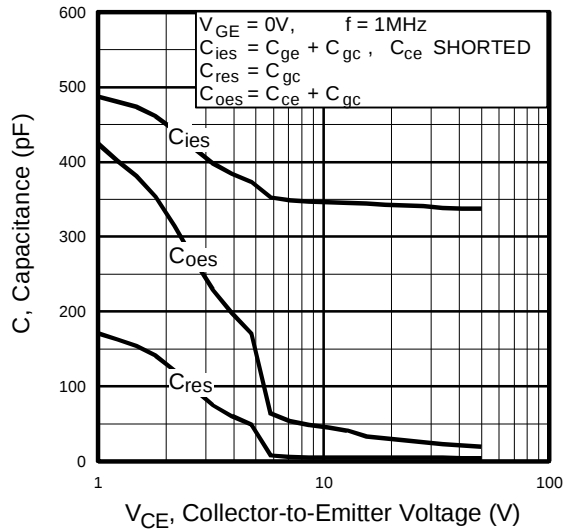


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

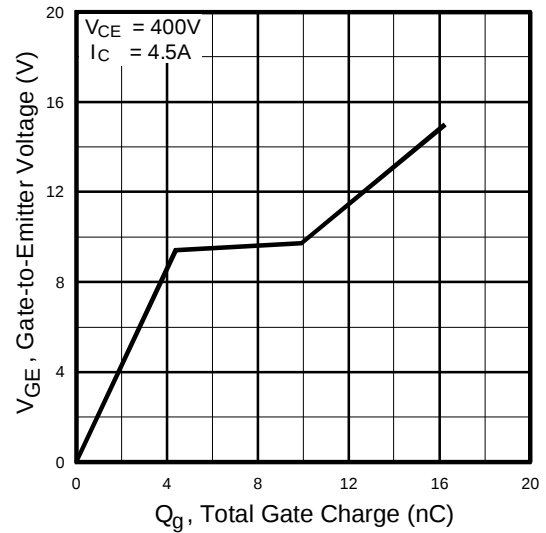


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

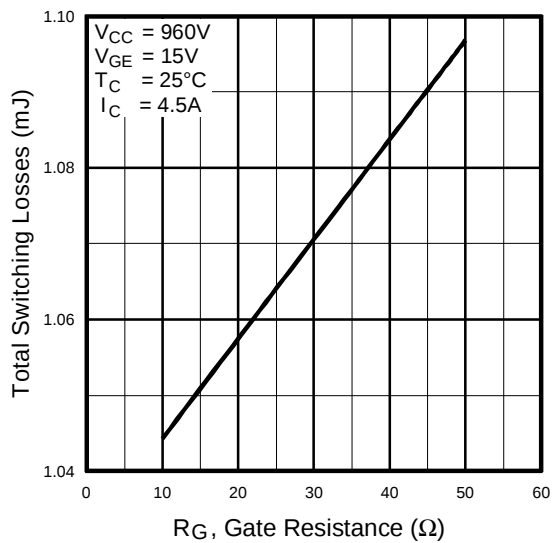


Fig. 9 - Typical Switching Losses vs. Gate Resistance

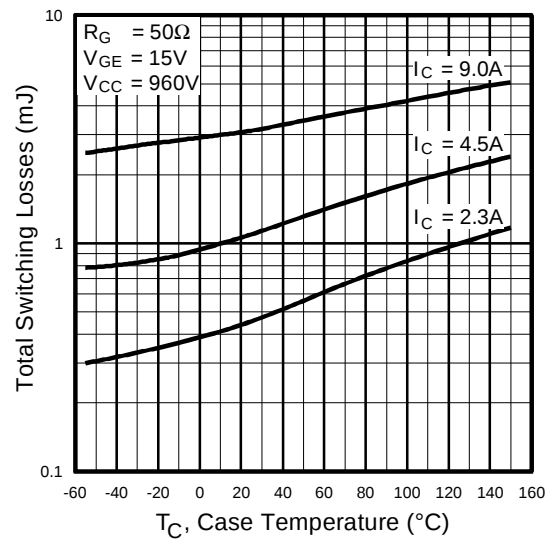


Fig. 10 - Typical Switching Losses vs. Case Temperature

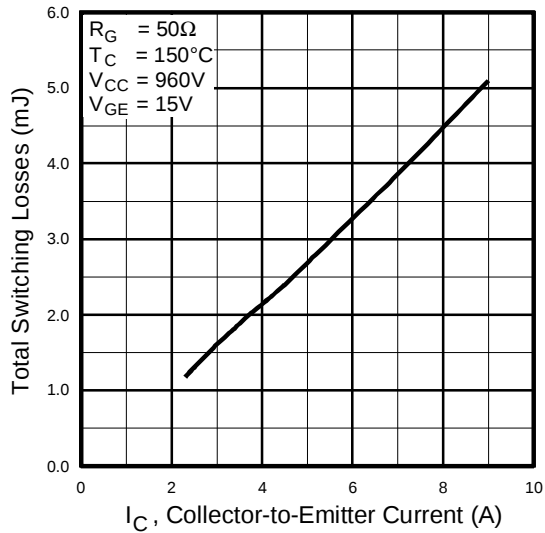


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

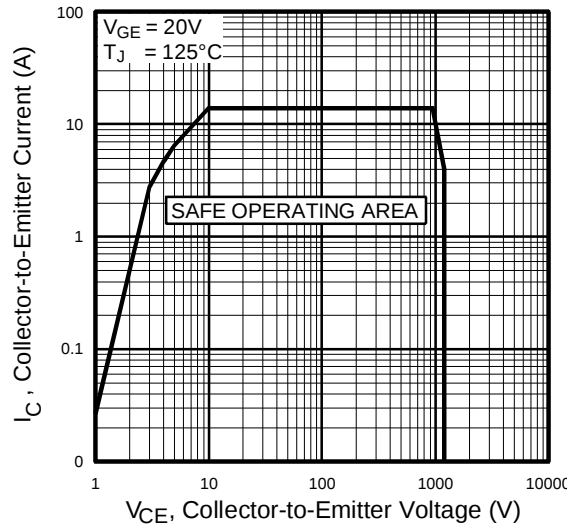


Fig. 12 - Turn-Off SOA

Refer to Section D for the following:

Appendix G: Section D - page D-9

- Fig. 13a - Clamped Inductive Load Test Circuit
- Fig. 13b - Pulsed Collector Current Test Circuit
- Fig. 14a - Switching Loss Test Circuit
- Fig. 14b - Switching Loss Waveform

Package Outline 3 - JEDEC Outline TO-247AC

Section D - page D-13